L Number	Hits		DB	Time stamp
1	16613	(etch\$3 remov\$3) near3 oxide same metal	USPAT;	2003/09/16 12:13
			US-PGPUB; EPO; JPO; DERWENT	
2	696	((etch\$3 remov\$3) near3 oxide same metal)	USPAT;	2003/09/16 09:01
2	050	and polish\$3 near3 metal	US-PGPUB;	
		and politings model	EPO; JPO;	
			DERWENT	
3	0	(((etch\$3 remov\$3) near3 oxide same metal)	USPAT;	2003/09/16 09:02
		and polish\$3 near3 metal) and	US-PGPUB;	
1		\$5flourocarbon	EPO; JPO; DERWENT	
4	0	(((etch\$3 remov\$3) near3 oxide same metal) and polish\$3 near3 metal) and	USPAT;	2003/09/16 09:02
			US-PGPUB;	
		\$5flourocarbon\$1	EPO; JPO;	
			DERWENT	
5	0	(((etch\$3 remov\$3) near3 oxide same metal)	USPAT;	2003/09/16 09:02
		and polish\$3 near3 metal) and flourocarbon\$1	US-PGPUB; EPO; JPO;	
1		Tiourocarbonsi	DERWENT	
6	27	(((etch\$3 remov\$3) near3 oxide same metal)	USPAT;	2003/09/16 10:18
J 1	- '	and polish\$3 near3 metal) and	US-PGPUB;	
		\$5fluorocarbon\$1	EPO; JPO;	
		( ) 102 ( ) ( ) ( )	DERWENT	2002/00/16 10 10
7	5295	(etch\$3 remov\$3) near5 metal near oxide	USPAT; US-PGPUB;	2003/09/16 10:18
			EPO; JPO;	
			DERWENT	
8	150	((etch\$3 remov\$3) near5 metal near oxide)	USPAT;	2003/09/16 11:50
		and \$5fluorocarbon\$1	US-PGPUB;	
			EPO; JPO;	
9	1	etch\$3 near5 metal near oxide same ph same	DERWENT USPAT;	2003/09/16 11:51
	7	(potassium near hydroxide koh)	US-PGPUB;	2000,03,10 11.01
		(FOOD 10 10 10 10 10 10 10 10 10 10 10 10 10	EPO; JPO;	
			DERWENT	
10	6	_	USPAT;	2003/09/16 11:55
		(potassium near hydroxide koh)	US-PGPUB; EPO; JPO;	
			DERWENT	
11	94464	etch\$3 near5 metal near oxide an ph and	USPAT;	2003/09/16 11:55
		(potassium near hydroxide koh)	US-PGPUB;	
			EPO; JPO; DERWENT	
12	27	etch\$3 near5 metal near oxide and ph and	USPAT;	2003/09/16 11:55
12	2,	(potassium near hydroxide koh)	US-PGPUB;	2000,00,10 11,00
			EPO; JPO;	
			DERWENT	0000/00/16 10 00
13	21	(etch\$3 near5 metal near oxide and ph and (potassium near hydroxide koh)) not	USPAT; US-PGPUB;	2003/09/16 12:02
		(etch\$3 near5 metal near oxide same ph and	EPO; JPO;	
ĺ		(potassium near hydroxide koh))	DERWENT	
14	317	438/754.ccls.	USPAT;	2003/09/16 12:03
			US-PGPUB;	
			EPO; JPO; DERWENT	
15	18	438/754.ccls. and ph and etch\$3 near3	USPAT;	2003/09/16 12:10
		oxide	US-PGPUB;	, , , , , , , , , , , , , , , , , , , ,
			EPO; JPO;	
1.0			DERWENT	0000 /00 /16 10 11
16	6	etch\$3 near (cuo copper near oxide tungsten near oxide) same ph	USPAT; US-PGPUB;	2003/09/16 12:10
		cungsten hear oxide) same ph	EPO; JPO;	
			DERWENT	
17	66	etch\$3 near3 oxide same metal same ph	USPAT;	2003/09/16 12:13
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	

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-	9162	polish\$3 near4 metal and (cu copper w tungsten al aluminum)	USPAT; US-PGPUB; EPO; JPO;	2003/09/16 09:00
_	1400	(polish\$3 near4 metal and (cu copper w tungsten al aluminum)) and (remov\$3 clean\$3 etch\$3) near4 oxide	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/07/10 07:51
_	1177	((polish\$3 near4 metal and (cu copper w tungsten al aluminum)) and (remov\$3	DERWENT USPAT; US-PGPUB;	2003/07/10 07:51
-	984	clean\$3 etch\$3) near4 oxide) and semiconductor (((polish\$3 near4 metal and (cu copper w tungsten al aluminum)) and (remov\$3 clean\$3 etch\$3) near4 oxide) and semiconductor) and chemical near	EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/10 07:52
-	68	tungsten al aluminum)) and (remov\$3 clean\$3 etch\$3) near4 oxide) and semiconductor) and chemical near mechanical) and (fluorocarbon\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/10 07:53
-	186	hydrofluorocarbon\$1) ((((polish\$3 near4 metal and (cu copper w tungsten al aluminum)) and (remov\$3 clean\$3 etch\$3) near4 oxide) and semiconductor) and chemical near mechanical) and (potassium near hydroxide koh)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/15 12:56
-	1 9	("5,527,423").PN. ("5478436"   "5482174"   "5645737"   "5830280"   "5972862"   "6043206"   "6090214"   "6162301"   "6171405").PN.	USPAT USPAT	2003/07/10 09:56 2003/07/10 09:25
_	22		USPAT	2003/07/10 09:27
-	2745		USPAT	2003/07/10 09:41
_	2745		USPAT	2003/07/10 09:57
-	209	((polish\$3 near4 metal and (cu copper w tungsten al aluminum)) and (remov\$3 clean\$3 etch\$3) near4 oxide) and 438/691-693,695,722,723,724.ccls.	USPAT	2003/07/10 09:57
-	145	(((polish\$3 near4 metal and (cu copper w tungsten al aluminum)) and (remov\$3 clean\$3 etch\$3) near4 oxide) and 438/691-693,695,722,723,724.ccls. ) not ((((polish\$3 near4 metal and (cu copper w tungsten al aluminum)) and (remov\$3 clean\$3 etch\$3) near4 oxide) and semiconductor) and chemical near	USPAT	2003/07/10 09:58
-	13	mechanical) and (potassium near hydroxide koh)) (("6383934") or ("5934980") or ("6162301") or ("6265781") or ("5981454") or ("6546939") or ("6432825") or ("6464568") or ("5482174") or ("6171405") or ("5954997") or ("5934980") or ("5806126") or ("5830280")).PN.	USPAT	2003/09/15 12:57